

**Micro Commercial Components** 

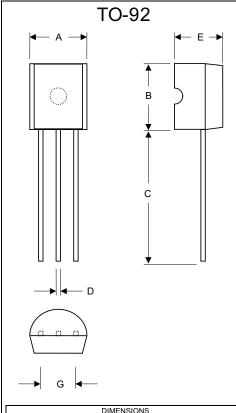
Micro Commercial Components 20736 Marilla Street Chatsworth CA 91311

Phone: (818) 701-4933 Fax: (818) 701-4939 S9012 S9012-G S9012-H S9012-I

## **Features**

- TO-92 Plastic-Encapsulate Transistors
- Capable of 0.625Watts(Tamb=25°C) of Power Dissipation.
- Collector-current 0.5A
- Collector-base Voltage 40V
- Operating and storage junction temperature range: -55°C to +150°C
- Marking: S9012
- Lead Free Finish/RoHS Compliant ("P" Suffix designates RoHS Compliant. See ordering information)
- Case Material: Molded Plastic. UL Flammability Classification Rating 94V-0 and MSL Rating 1

# PNP Silicon Transistors



DIMENSIONS					
	INCHES		MM		
DIM	MIN	MAX	MIN	MAX	NOTE
Α	.170	.190	4.33	4.83	
В	.170	.190	4.30	4.83	
С	.550	.590	13.97	14.97	
D	.010	.020	0.36	0.56	
E	.130	.160	3.30	3.96	
G	.010	.104	2.44	2.64	

# Electrical Characteristics @ 25°C Unless Otherwise Specified

Symbol	Parameter	Min	Max	Units
OFF CHARACTERISTICS				
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage (b=100uAdc, l=0)	40		Vdc
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage (b=0.1mAdc, b=0)	25		Vdc
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage ( <sub>E</sub> =100uAdc, <sub>Ic</sub> =0)	5.0		Vdc
I <sub>CBO</sub>	Collector Cutoff Current (V <sub>CB</sub> =40Vdc, ½=0)		0.1	uAdc
Iceo	Collector Cutoff Current (V <sub>CE</sub> =20Vdc, <sub>b</sub> =0)		0.2	uAdc
I <sub>EBO</sub>	Emitter Cutoff Current (V <sub>EB</sub> =5.0Vdc,		0.1	uAdc
ON CHARACTERISTICS				
h <sub>FE(1)</sub>	DC Current Gain (h=1mAdc, Vc==4.0Vdc)	64	400	

h <sub>FE(1)</sub>	DC Current Gain	64	400	
	(l <sub>c</sub> =1mAdc, V <sub>cE</sub> =4.0Vdc)			
h <sub>FE(2)</sub>	DC Current Gain	40		
	(├=500mAdc, V <sub>CE</sub> =1.0Vdc)			
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage		0.6	Vdc
	( $l_c$ =500mAdc, $l_B$ =50mAdc)			
$V_{BE(sat)}$	Base-Emitter Saturation Voltage		1.2	Vdc
	(l <sub>c</sub> =500mAdc, l <sub>s</sub> =50mAdc)			
V <sub>EB</sub>	Base- Emitter Voltage		1.4	Vdc
	( <u></u> =100mAdc)			

#### SMALL-SIGNAL CHARACTERISTICS

f⊤	Transistor Frequency	150		MHz
	( $b=20$ mAdc, $V_{CE}=6.0$ Vdc, $f=30$ MHz)			

#### CLASSIFICATION OF HEED

Rank	G	Н	1	
Range	112 -166	144 -202	190 -300	

www.mccsemi.com



### **Ordering Information**

Device	Packing	
(Part Number)-AP	Tape&Reel2Kpcs/Box	
(Part Number)-BP	Bulk;1Kpcs/Bag	

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